

BC546B, BC547A, B, C, BC548B, C

Amplifier Transistors

NPN Silicon

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage BC546 BC547 BC548	V_{CEO}	65 45 30	Vdc
Collector - Base Voltage BC546 BC547 BC548	V_{CBO}	80 50 30	Vdc
Emitter - Base Voltage	V_{EBO}	6.0	Vdc
Collector Current - Continuous	I_C	100	mA dc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

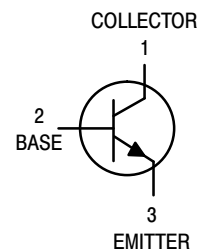
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

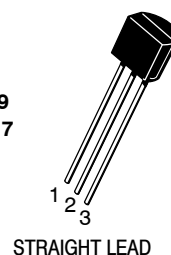


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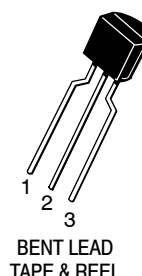
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TO-92
CASE 29
STYLE 17

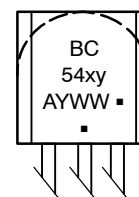


STRAIGHT LEAD



BENT LEAD
TAPE & REEL

MARKING DIAGRAM



- x = 6, 7, or 8
- y = A, B or C
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BC546B, BC547A, B, C, BC548B, C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = 1.0 mA, I _B = 0)	V _{(BR)CEO}	65 45 30	– – –	– – –	V
Collector – Base Breakdown Voltage (I _C = 100 µA)	V _{(BR)CBO}	80 50 30	– – –	– – –	V
Emitter – Base Breakdown Voltage (I _E = 10 µA, I _C = 0)	V _{(BR)EBO}	6.0 6.0 6.0	– – –	– – –	V
Collector Cutoff Current (V _{CE} = 70 V, V _{BE} = 0) (V _{CE} = 50 V, V _{BE} = 0) (V _{CE} = 35 V, V _{BE} = 0) (V _{CE} = 30 V, T _A = 125°C)	I _{CES}	– – – –	0.2 0.2 0.2 –	15 15 15 4.0	nA µA

ON CHARACTERISTICS

DC Current Gain (I _C = 10 µA, V _{CE} = 5.0 V)	BC547A BC546B/547B/548B BC548C	h _{FE}	– – –	90 150 270	– – –	–
(I _C = 2.0 mA, V _{CE} = 5.0 V)	BC546 BC547 BC548 BC547A BC546B/547B/548B BC547C/BC548C		110 110 110 110 200 420	– – – 180 290 520	450 800 800 220 450 800	
(I _C = 100 mA, V _{CE} = 5.0 V)	BC547A/548A BC546B/547B/548B BC548C		– – –	120 180 300	– – –	
Collector – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA) (I _C = 10 mA, I _B = See Note 1)		V _{CE(sat)}	– – –	0.09 0.2 0.3	0.25 0.6 0.6	V
Base – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA)		V _{BE(sat)}	–	0.7	–	V
Base – Emitter On Voltage (I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 10 mA, V _{CE} = 5.0 V)		V _{BE(on)}	0.55 –	– –	0.7 0.77	V

SMALL-SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 V, f = 100 MHz)	BC546 BC547 BC548	f _T	150 150 150	300 300 300	– – –	MHz
Output Capacitance (V _{CB} = 10 V, I _C = 0, f = 1.0 MHz)		C _{obo}	–	1.7	4.5	pF
Input Capacitance (V _{EB} = 0.5 V, I _C = 0, f = 1.0 MHz)		C _{ibo}	–	10	–	pF
Small – Signal Current Gain (I _C = 2.0 mA, V _{CE} = 5.0 V, f = 1.0 kHz)	BC546 BC547/548 BC547A BC546B/547B/548B BC547C/548C	h _{fe}	125 125 125 240 450	– – 220 330 600	500 900 260 500 900	–
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 V, R _S = 2 kΩ, f = 1.0 kHz, Δf = 200 Hz)	BC546 BC547 BC548	NF	– – –	2.0 2.0 2.0	10 10 10	dB

1. I_B is value for which I_C = 11 mA at V_{CE} = 1.0 V.

BC546B, BC547A, B, C, BC548B, C

BC547/BC548

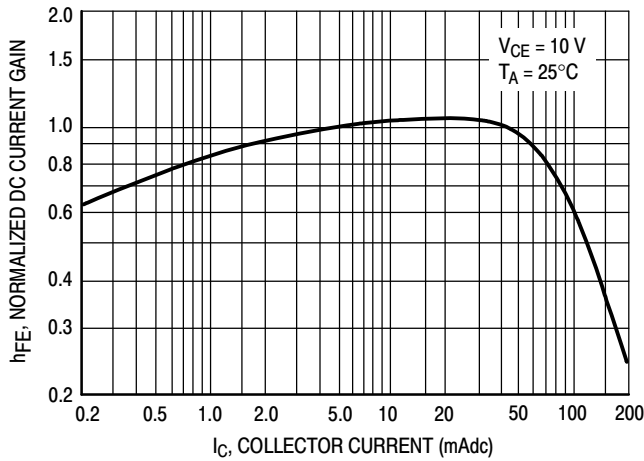


Figure 1. Normalized DC Current Gain

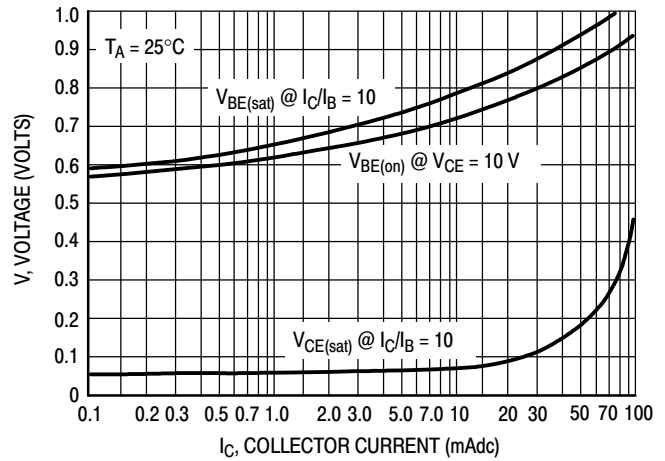


Figure 2. "Saturation" and "On" Voltages

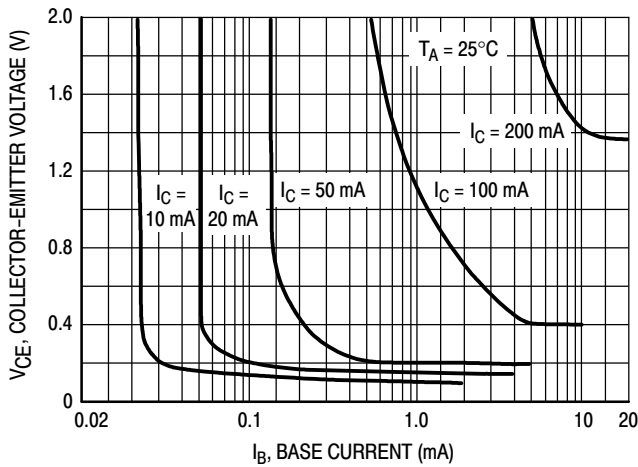


Figure 3. Collector Saturation Region

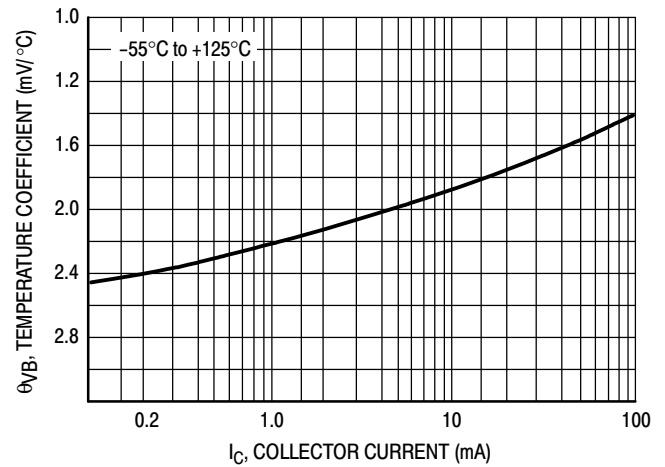


Figure 4. Base-Emitter Temperature Coefficient

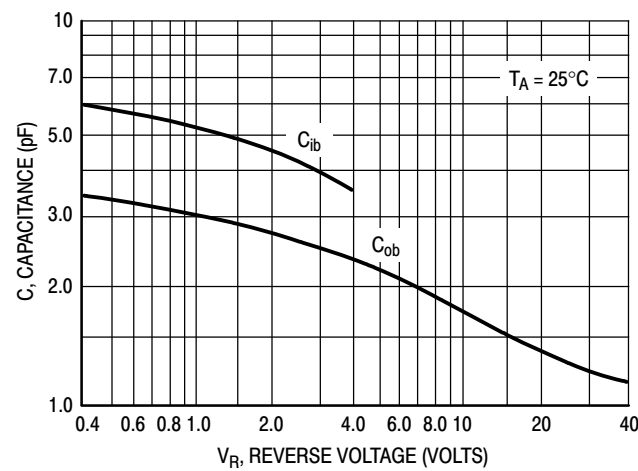


Figure 5. Capacitances

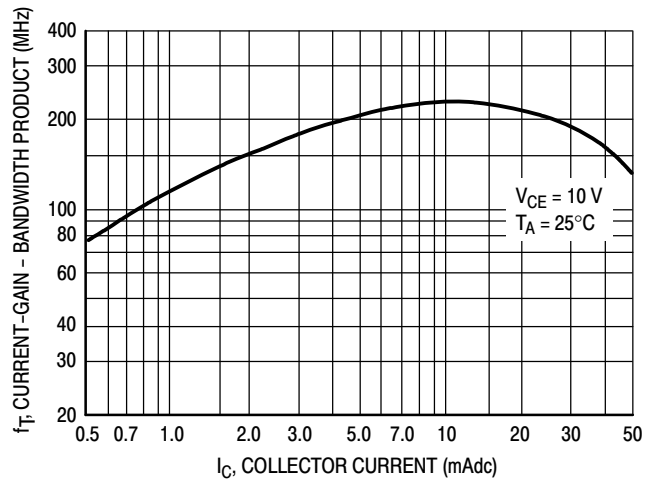


Figure 6. Current-Gain - Bandwidth Product

BC546B, BC547A, B, C, BC548B, C

BC546

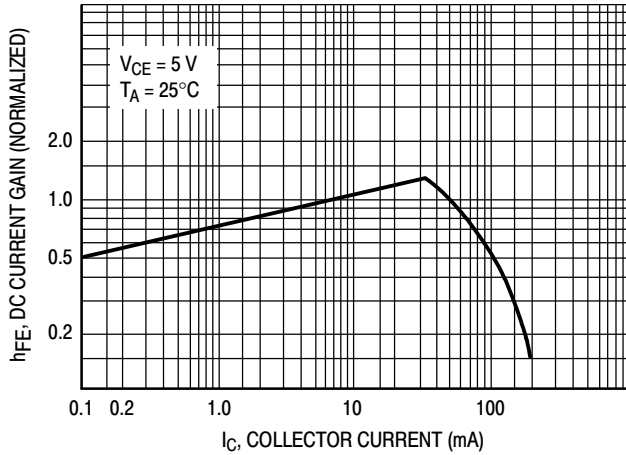


Figure 7. DC Current Gain

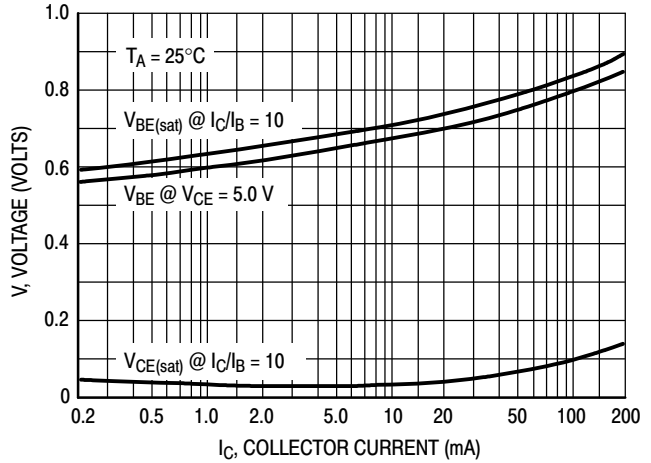


Figure 8. "On" Voltage

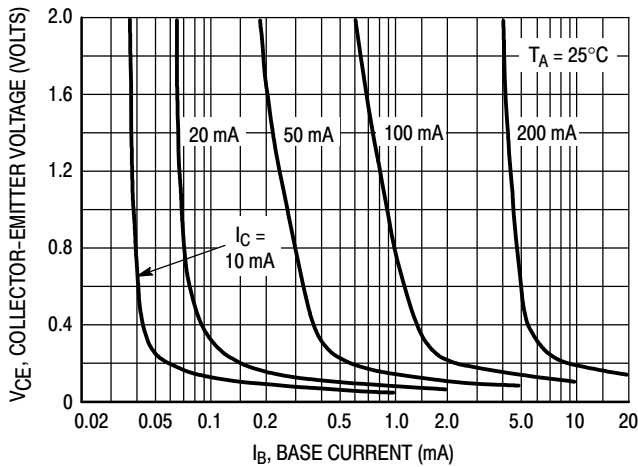


Figure 9. Collector Saturation Region

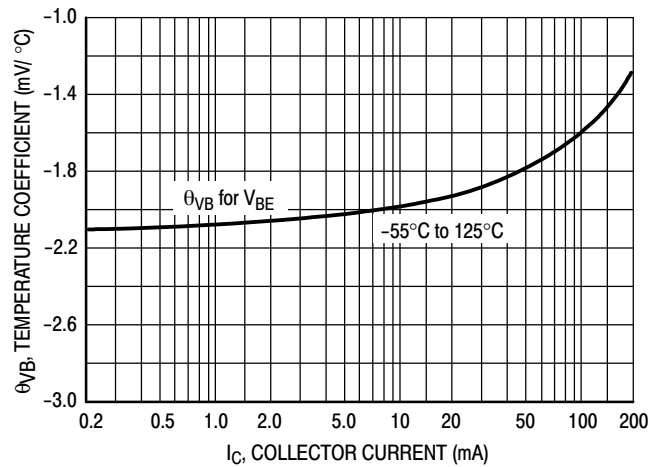


Figure 10. Base-Emitter Temperature Coefficient

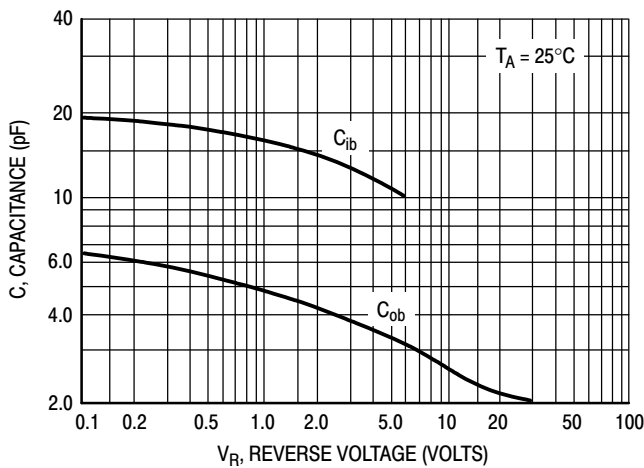


Figure 11. Capacitance

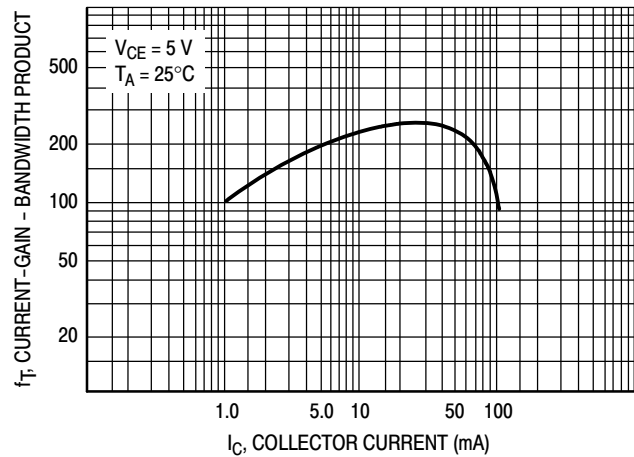


Figure 12. Current-Gain - Bandwidth Product

BC546B, BC547A, B, C, BC548B, C

ORDERING INFORMATION

Device	Package	Shipping [†]
BC546B	TO-92	5000 Units / Bulk
BC546BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC546BRL1	TO-92	2000 / Tape & Reel
BC546BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC546BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC547ARL	TO-92	2000 / Tape & Reel
BC547ARLG	TO-92 (Pb-Free)	2000 / Tape & Reel
BC547AZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC547BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC547BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC547BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC547CG	TO-92 (Pb-Free)	5000 Units / Bulk
BC547CZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC548BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC548BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC548BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC548CG	TO-92 (Pb-Free)	5000 Units / Bulk
BC548CZL1G	TO-92 (Pb-Free)	2000 / Ammo Box

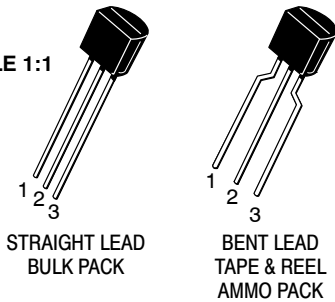
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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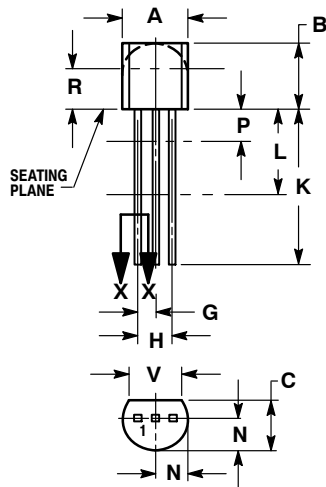
ON

SCALE 1:1

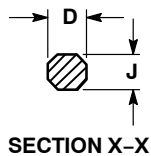


TO-92 (TO-226)
CASE 29-11
ISSUE AM

DATE 09 MAR 2007



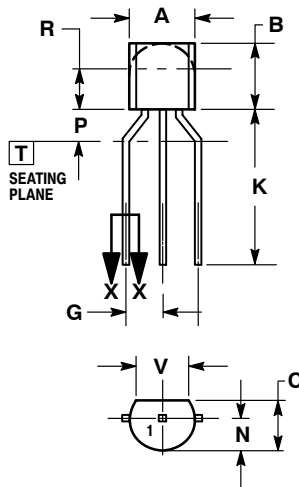
STRAIGHT LEAD
BULK PACK



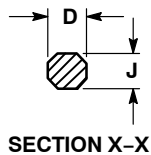
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD
TAPE & REEL
AMMO PACK



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLES ON PAGE 2

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CASE 29-11
ISSUE AM

DATE 09 MAR 2007

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 2: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. DRAIN 2. SOURCE 3. GATE
STYLE 6: PIN 1. GATE 2. SOURCE & SUBSTRATE 3. DRAIN	STYLE 7: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 8: PIN 1. DRAIN 2. GATE 3. SOURCE & SUBSTRATE	STYLE 9: PIN 1. BASE 1 2. EMITTER 3. BASE 2	STYLE 10: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 11: PIN 1. ANODE 2. CATHODE & ANODE 3. CATHODE	STYLE 12: PIN 1. MAIN TERMINAL 1 2. GATE 3. MAIN TERMINAL 2	STYLE 13: PIN 1. ANODE 1 2. GATE 3. CATHODE 2	STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE	STYLE 15: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2
STYLE 16: PIN 1. ANODE 2. GATE 3. CATHODE	STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER	STYLE 18: PIN 1. ANODE 2. CATHODE 3. NOT CONNECTED	STYLE 19: PIN 1. GATE 2. ANODE 3. CATHODE	STYLE 20: PIN 1. NOT CONNECTED 2. CATHODE 3. ANODE
STYLE 21: PIN 1. COLLECTOR 2. EMITTER 3. BASE	STYLE 22: PIN 1. SOURCE 2. GATE 3. DRAIN	STYLE 23: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 24: PIN 1. EMITTER 2. COLLECTOR/ANODE 3. CATHODE	STYLE 25: PIN 1. MT 1 2. GATE 3. MT 2
STYLE 26: PIN 1. V_{CC} 2. GROUND 2 3. OUTPUT	STYLE 27: PIN 1. MT 2. SUBSTRATE 3. MT	STYLE 28: PIN 1. CATHODE 2. ANODE 3. GATE	STYLE 29: PIN 1. NOT CONNECTED 2. ANODE 3. CATHODE	STYLE 30: PIN 1. DRAIN 2. GATE 3. SOURCE
STYLE 31: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 32: PIN 1. BASE 2. COLLECTOR 3. EMITTER	STYLE 33: PIN 1. RETURN 2. INPUT 3. OUTPUT	STYLE 34: PIN 1. INPUT 2. GROUND 3. LOGIC	STYLE 35: PIN 1. GATE 2. COLLECTOR 3. EMITTER

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